



ON Semiconductor®

# FDC6327C

## Dual N & P-Channel 2.5V Specified PowerTrench™ MOSFET

### General Description

These N & P-Channel 2.5V specified MOSFETs are produced using ON Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

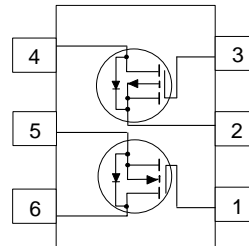
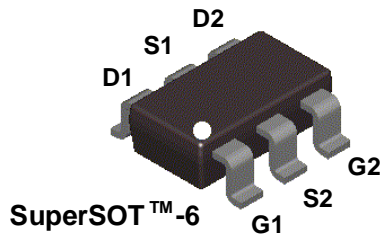
These devices have been designed to offer exceptional power dissipation in a very small footprint for applications where the bigger more expensive SO-8 and TSSOP-8 packages are impractical.

### Applications

- DC/DC converter
- Load switch
- Motor driving

### Features

- N-Channel 2.7A, 20V.  $R_{DS(on)} = 0.08\Omega @ V_{GS} = 4.5V$   
 $R_{DS(on)} = 0.12\Omega @ V_{GS} = 2.5V$
- P-Channel -1.6A, -20V.  $R_{DS(on)} = 0.17\Omega @ V_{GS} = -4.5V$   
 $R_{DS(on)} = 0.25\Omega @ V_{GS} = -2.5V$
- Fast switching speed.
- Low gate charge.
- High performance trench technology for extremely low  $R_{DS(on)}$ .
- SuperSOT™-6 package: small footprint (72% smaller than SO-8); low profile (1mm thick).



### Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	N-Channel	P-Channel	Units
V <sub>DSS</sub>	Drain-Source Voltage	20	-20	V
V <sub>GSS</sub>	Gate-Source Voltage	±8	±8	V
I <sub>D</sub>	Drain Current - Continuous (Note 1a) - Pulsed	2.7 8	-1.9 -8	A
P <sub>D</sub>	Power Dissipation (Note 1a) (Note 1b) (Note 1c)	0.96 0.9 0.7		W
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150		°C

### Thermal Characteristics

R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 1a)	130	°C/W
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case (Note 1)	60	°C/W

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
.327	FDC6327C	7"	8mm	3000

### Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
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#### Off Characteristics

$V_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$ $V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	N-Ch P-Ch	20 -20			V
$\frac{\Delta V_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$ $I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	N-Ch P-Ch		12 -19		$\text{mV}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 16\text{ V}, V_{GS} = 0\text{ V}$ $V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$	N-Ch P-Ch			1 -1	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage, Forward	$V_{GS} = 8\text{ V}, V_{DS} = 0\text{ V}$	All			100	nA
$I_{GSSR}$	Gate-Body Leakage, Reverse	$V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$	All			-100	nA

#### On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$ $V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	N-Ch P-Ch	0.4 -0.4	0.9 -0.9	1.5 -1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$ $I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	N-Ch P-Ch		-2.1 2.3		$\text{mV}/^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 4.5\text{ V}, I_D = 2.7\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 2.7\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = 2.5\text{ V}, I_D = 2.2\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -1.6\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -1.6\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = -2.5\text{ V}, I_D = -1.3\text{ A}$	N-Ch N-Ch N-Ch P-Ch P-Ch P-Ch		0.069 0.094 0.093 0.141 0.203 0.205	0.08 0.13 0.12 0.17 0.27 0.25	$\Omega$
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 4.5\text{ V}, V_{DS} = 5\text{ V}$ $V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	N-Ch P-Ch	8 -8			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 2.7\text{ A}$ $V_{DS} = -5\text{ V}, I_D = -1.9\text{ A}$	N-Ch P-Ch		7.7 4.5		S

#### Dynamic Characteristics

$C_{iss}$	Input Capacitance	N-Channel $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$	N-Ch P-Ch		325 315		pF
$C_{oss}$	Output Capacitance	P-Channel	N-Ch P-Ch		75 65		pF
$C_{rss}$	Reverse Transfer Capacitance	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$	N-Ch P-Ch		35 24		pF

**Electrical Characteristics (continued)**  $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
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**Switching Characteristics** (Note 2)

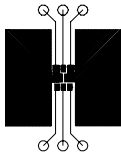
$t_{d(on)}$	Turn-On Delay Time	N-Channel $V_{DD} = 10\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 4.5\text{ V}, R_{GEN} = 6\ \Omega$	N-Ch P-Ch		5 7	15 14	ns
$t_r$	Turn-On Rise Time		N-Ch P-Ch		9 14	18 25	ns
$t_{d(off)}$	Turn-Off Delay Time	P-Channel $V_{DD} = -10\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$	N-Ch P-Ch		12 14	22 25	ns
$t_f$	Turn-Off Fall Time		N-Ch P-Ch		3 3	9 9	ns
$Q_g$	Total Gate Charge	N-Channel $V_{DS} = 10\text{ V}, I_D = 2.7\text{ A}, V_{GS} = 4.5\text{ V}$	N-Ch P-Ch		3.25 2.85	4.5 4.0	nC
$Q_{gs}$	Gate-Source Charge		N-Ch P-Ch		0.65 0.68		nC
$Q_{gd}$	Gate-Drain Charge	P-Channel $V_{DS} = -10\text{ V}, I_D = -1.9\text{ A}, V_{GS} = -4.5\text{ V}$	N-Ch P-Ch		0.90 0.65		nC

**Drain-Source Diode Characteristics and Maximum Ratings**

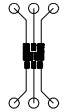
$I_S$	Maximum Continuous Drain-Source Diode Forward Current		N-Ch P-Ch			0.8 -0.8	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 0.8\text{ A}$ (Note 2) $V_{GS} = 0\text{ V}, I_S = -0.8\text{ A}$ (Note 2)	N-Ch P-Ch		0.76 -0.79	1.2 -1.2	V

**Notes:**

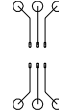
- 1:  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design. Both devices are assumed to be operating and sharing the dissipated heat energy equally.



a)  $130^\circ\text{C/W}$  when mounted on a  $0.125\text{ in}^2$  pad of 2 oz. copper.



b)  $140^\circ\text{C/W}$  when mounted on a  $0.005\text{ in}^2$  pad of 2 oz. copper.



c)  $180^\circ\text{C/W}$  when mounted on a  $0.0015\text{ in}^2$  pad of 2 oz. copper.

Scale 1 : 1 on letter size paper

- 2: Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

## Typical Characteristics: N-Channel

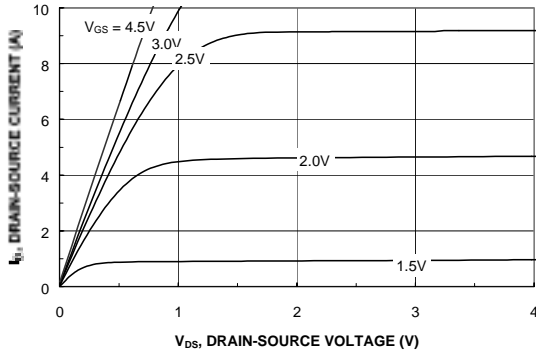


Figure 1. On-Region Characteristics.

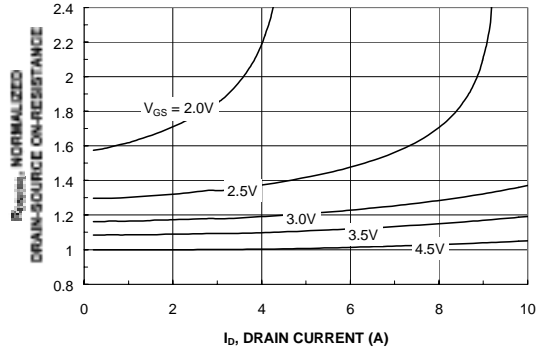


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

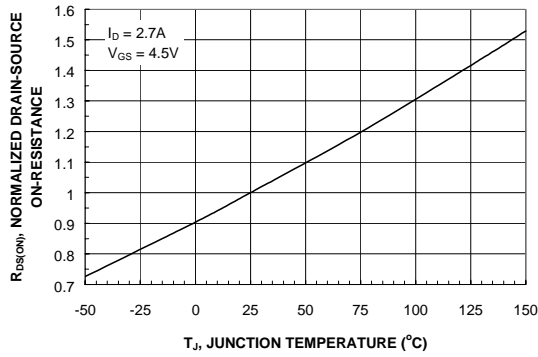


Figure 3. On-Resistance Variation with Temperature.

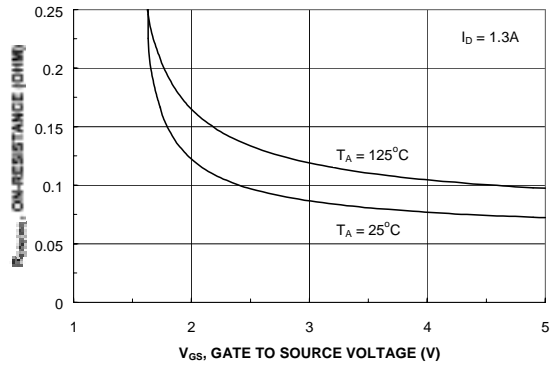


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

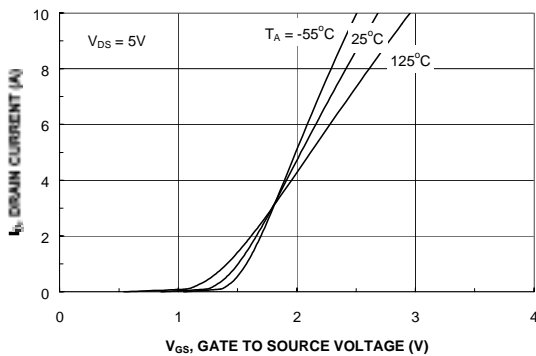


Figure 5. Transfer Characteristics.

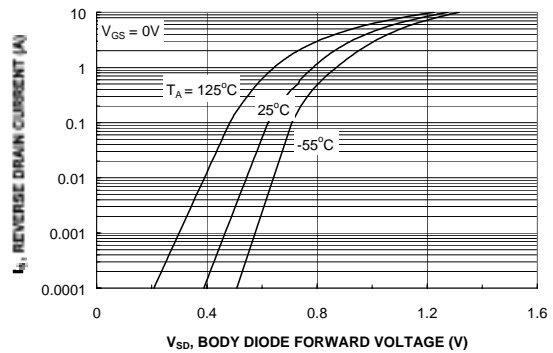
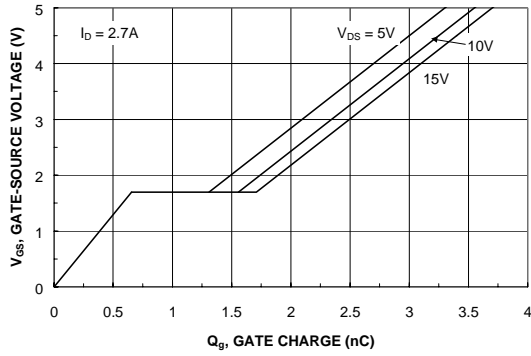
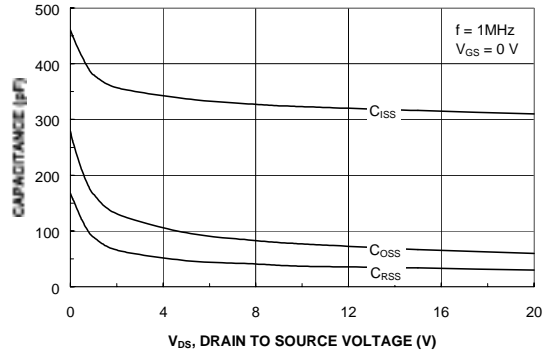


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

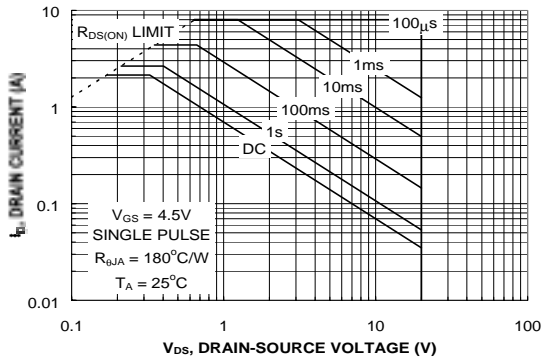
**Typical Characteristics: N-Channel** (continued)



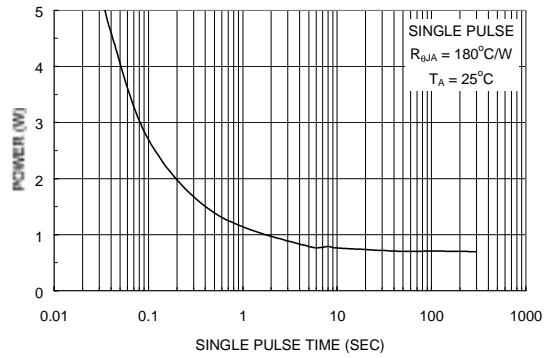
**Figure 7. Gate-Charge Characteristics.**



**Figure 8. Capacitance Characteristics.**



**Figure 9. Maximum Safe Operating Area.**



**Figure 10. Single Pulse Maximum Power Dissipation.**

### Typical Characteristics: P-Channel

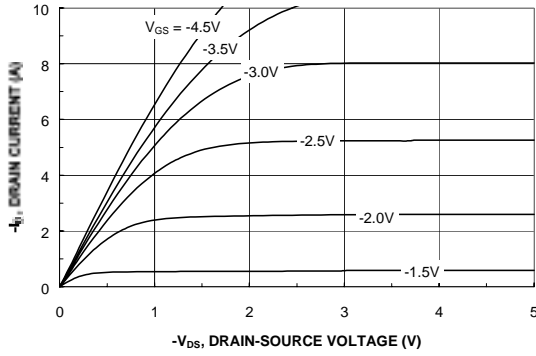


Figure 11. On-Region Characteristics.

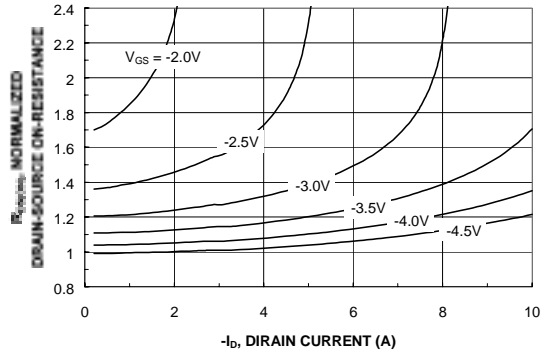


Figure 12. On-Resistance Variation with Drain Current and Gate Voltage.

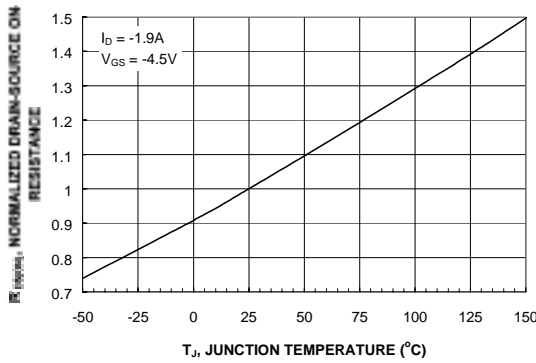


Figure 13. On-Resistance Variation with Temperature.

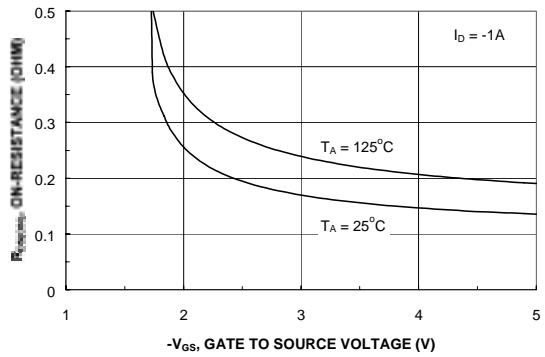


Figure 14. On-Resistance Variation with Gate-to-Source Voltage.

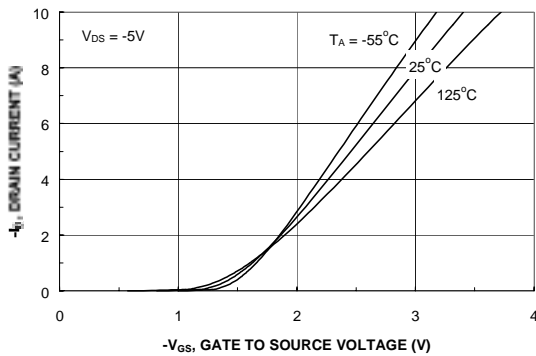


Figure 15. Transfer Characteristics.

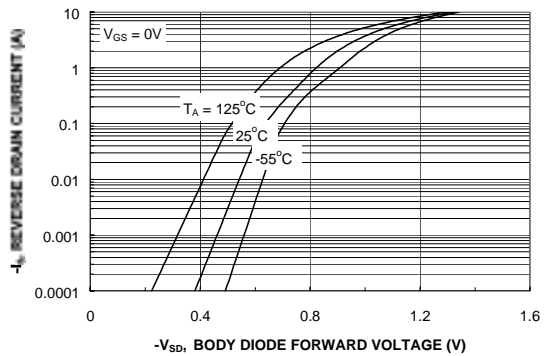
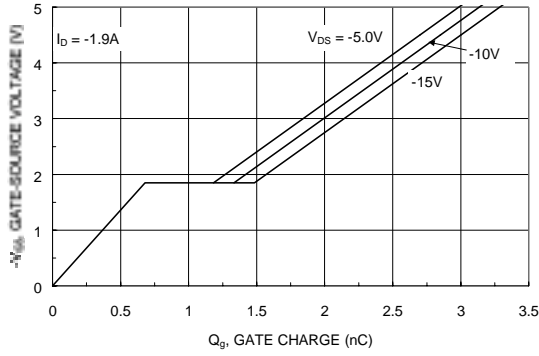
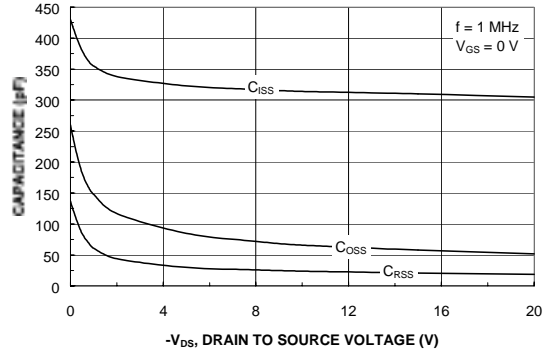


Figure 16. Body Diode Forward Voltage Variation with Source Current and Temperature.

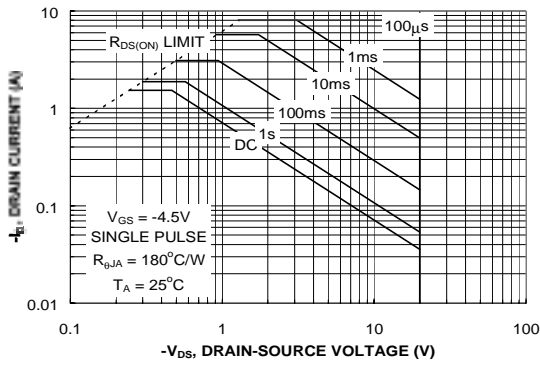
**Typical Characteristics: P-Channel** (continued)



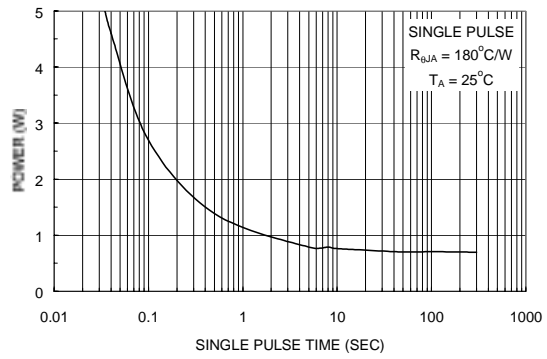
**Figure 17. Gate-Charge Characteristics.**



**Figure 18. Capacitance Characteristics.**



**Figure 19. Maximum Safe Operating Area.**



**Figure 20. Single Pulse Maximum Power Dissipation.**

Typical Characteristics: N & P-Channel (continued)

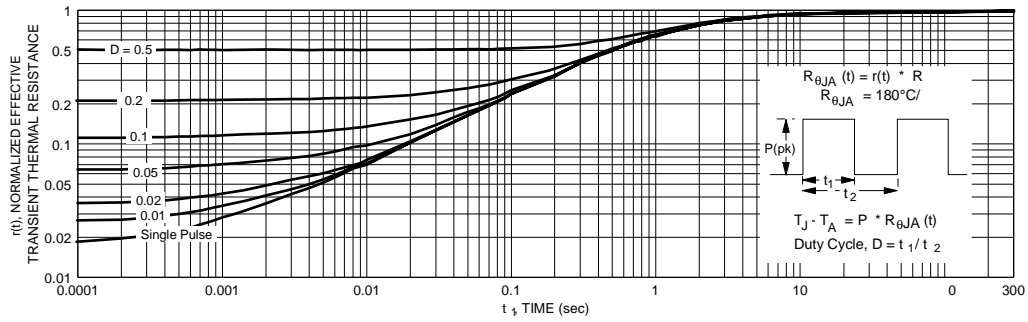


Figure 21. Transient Thermal Response Curve.



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